

Au8013A: 2A Ultra Low Noise, Ultra Low Dropout Regulator

General Description

The Au8013A is a low-noise (4.3 μ VRMS), low-dropout linear regulator (LDO) capable of sourcing 2A with only 100 mV of dropout. The device output voltage is pin-programmable from 0.8 V to 3.95 V and adjustable from 0.8 V to 5.15 V using an external resistor divider.

Au8013A is the ideal choice to power noise-sensitive components found in high speed interfaces such as SERDES, 5G communication infrastructure such as High Speed ADCs, DACs and RF components due to its exceptional PSRR and low noise (4.3 μ VRMS) characteristics. The high PSRR and low noise combination of Au8013A limits power-supply induced phase noise and clock jitter.

The 5 V output capability of this device is well suited for RF amplifiers and RF front end. The Au8013A device is also well suited for digital loads such as ASICs, FPGAs, and DSPs that require a low-input voltage and low-output voltage to minimize power dissipation while providing excellent transient performance that caters to current steps in digital loads due to clock domain switching, dynamic power and frequency scaling. The soft-start capability minimizes in-rush current, thereby allowing for a smooth and reliable start-up at the system level.

Features

- Low Dropout: 100 mV at 2 A
- 1% (max) Accuracy Over Line, Load and Temperature (3.5mm x 3.5mm package)
- Output Voltage Noise:
 - 4.3 μVRMS at 0.8 V Output
 - o 7.6 μVRMS at 5.0 V Output
- Input Voltage Range:
 - Without BIAS: 1.4 V to 6.5 V
 - With BIAS: 1.1 V to 6.5 V
- Two Output Voltage Modes
 - o 0.8 V to 5.15 V (Set by resistor divider)
 - 0.8 V to 3.95 V (Set via programming pins)
- Excellent PSRR of 38 dB at 1MHz
- Excellent Load Transient Response
- Adjustable Soft-Start In-Rush Control
- 3.5 mm x 3.5 mm, 20-Pin QFN
- 5mm x 5mm, 20-Pin QFN

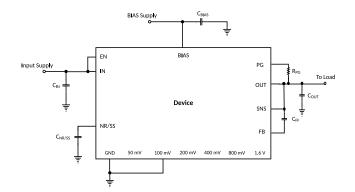


Figure 1 Application Schematic

Applications

- 5G MIMO RF front end components
- Digital Loads: SerDes, FPGAs and DSPs
- High-speed Analog Circuits:
 - VCO, ADC, DAC, and LVDS



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1 Pin Configuration

1.1 Pin Configuration Diagram

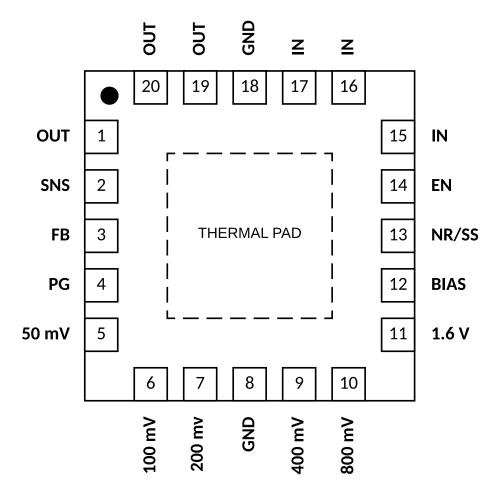


Figure 2 Au8013A Pin Configuration for 3.5mm x 3.5mm and 5mm x 5mm packages.

1.2Pin Description

Table 1 Pin Functions

Pin Name	Pin No.	I/O	Description		
50 mV	5		Programmable output voltage setting pins. Connect these pins to		
100 mV	6		ground, SNS, or leave floating. Connecting these pins to ground		
200 mV	7	١.	increases the output voltage, whereas connecting these pins to SNS		
400 mV	9	'	increases the resolution of the programmable network but decreases the range of the network; multiple pins can be simultaneously		
800 mV	10		connected to GND or SNS to select the desired output voltage. Leave		
1.6 V	11		these pins floating (open) when not in use.		
BIAS	12	ı	BIAS supply voltage. This pin enables the use of low-input voltage, low-output voltage conditions (that is, $V_{IN} = 1.1 \text{ V}$, $V_{OUT} = 0.8 \text{ V}$) to reduce power dissipation across the die. The use of a BIAS voltage improves dc and ac performance for $V_{IN} \le 1.4 \text{ V}$. A 10 μF capacitor or larger must be connected between this pin and ground. If not used, this pin must be left floating or tied to ground.		



Pin Name	Pin No.	I/O	Description
EN	14	I	Enable pin. Driving this pin to logic high enables the device; driving this pin to logic low disables the device. If enable functionality is not required, this pin must be connected to IN. If enable functionality is required, V _{EN} must go high after V _{IN} is established when a BIAS supply is used.
FB	3	I	Feedback pin connected to the error amplifier. Although not required, a 10 nF feed-forward capacitor from FB to OUT (as close to the device as possible) is recommended to maximize ac and noise performance.
GND	8, 18	_	Ground pin. These pins must be connected to ground, the thermal pad, and each other with a low-impedance connection.
IN	15-17	I	Input supply voltage pin. A 47 μ F or larger ceramic capacitor (25 μ F or greater of capacitance) from IN to ground is recommended to reduce the impedance of the input supply. Place the input capacitor as close to the input as possible.
NR/SS	13	_	Noise-reduction and soft-start pin. Connecting an external capacitor between this pin and ground reduces reference voltage noise and also enables the soft-start function. Although not required, a 10 nF or larger capacitor is recommended to be connected from NR/SS to GND (as close to the pin as possible) to maximize ac performance.
OUT	1, 19, 20	0	Regulated output pin. A 47 µF or larger ceramic capacitor (25 µF or greater of capacitance) from OUT to ground is required for stability and must be placed as close to the output as possible. Minimize the impedance from the OUT pin to the load.
PG	4	0	Active-high, power-good pin. An open-drain output indicates when the output voltage reaches 89.3% of the target. The use of a feed-forward capacitor can disrupt PG (power good) functionality.
SNS	2	I	Output voltage sense input pin. This pin connects the internal R ₁ resistor to the output. Connect this pin to the load side of the output trace only if the programmable output feature is used.
Thermal pad		_	Connect the thermal pad to a large-area ground plane. The thermal pad is internally connected to GND.

2 Electrical Specifications

Table 2 Absolute Maximum Ratings

Over junction temperature range (unless otherwise noted) [1]

Parameter	Pin	Min	Max	Units
	IN, BIAS, PG, EN	-0.3	7.0	V
	SNS, OUT	-0.3	V _{IN} +0.3 [2]	V
Voltage	NR/SS, FB	-0.3	3.6	V
	50 mV, 100 mV, 200 mV, 400 mV,		Vour 1 0 3	V
	· · · · · · · · · · · · · · · · · · ·	V001 + 0.3	V	
Current	OUT	Internally lim	Internally limited	
Current	PG (sink current into device)		5	mA
Operating junction temperature, T _J		-40	125	°C
Storage temperature, T _{STG}		- 55	160	°C

Notes:

- Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings
 only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Table 3.
 Exposure to absolute maximum rated conditions for extended periods may affect device reliability.
- 2. The absolute maximum rating is VIN +0.3 V or 7.0 V, whichever is smaller.

Table 3 ESD Ratings

Parameter	Conditions	Symbols	Value	Units
Electro Static Discharge	Human Body Model	\/	±2000	V
Electio Static Discharge	Charged Body Model	VESD	±500	V



Table 4 Recommended Operating Conditions

Over junction temperature range (unless otherwise noted)

Parameter	Symbol	Min	Тур	Max	Unit
Input supply voltage range	V _{IN}	1.1		6.5	V
Bias supply voltage range [1]	V _{BIAS}	3.0		6.5	V
Output voltage range [2]	Vouт	0.8		5.15	V
Enable voltage range	V _{EN}	0		V _{IN}	V
Output current	Іоит	0		3	А
Input capacitor	Cin	10	47		μF
Output capacitor	Соит	47	47 10 10 ³		μF
Power-good pullup resistance	R _{PG}	10		100	kΩ
NR/SS capacitor	C _{NR/SS}		10		nF
Feed-forward capacitor	C _{FF}		10		nF
Operating junction temperature	TJ	-40		125	°C

Notes:

- 1. BIAS supply is required when the V_{IN} supply is below 1.4 V. Conversely, no BIAS supply is required when the V_{IN} supply is higher than or equal to 1.4 V. A BIAS supply helps improve dc and ac performance for $V_{IN} \le 1.4$ V.
- 2. This output voltage range does not include device accuracy or accuracy of the feedback resistors.
- The recommended output capacitors are selected to optimize PSRR for the frequency range of 900 kHz to 1.1MHz. This frequency range is a typical value for DC-DC supplies.

Table 5 Thermal Information

Thermal Metric	Symbol	3.5mm x 3.5mm pkg	Unit
Junction-to-ambient thermal resistance	Reja	35.4	°C/W
Junction-to-case(top) thermal resistance	Rejc	27.9	°C/W
Junction-to-board thermal resistance	Rејв	26.59	°C/W
Junction-to-top characterization parameter	ΨθЈТ	0.39	°C/W

Thermal Metric	Symbol	5mmx 5mm pkg	Unit
Junction-to-ambient thermal resistance	R _{θJA}	33.6	°C/W
Junction-to-case(top) thermal resistance	Rejc	27.9	°C/W
Junction-to-board thermal resistance	R _θ ЈВ	26.59	°C/W
Junction-to-top characterization parameter	ΨθЈТ	0.39	°C/W

Table 6 Electrical Specifications

Over operating junction temperature range (T $_J$ = -40 °C to +125 °C), V_{IN} = 1.4 V or V_{IN} = $V_{OUT(nom)}$ + 0.4 V (whichever is greater), V_{BIAS} = open, $V_{OUT(nom)}$ = 0.8 V $^{[1]}$, V_{EN} = 1.1 V, C_{IN} = 10 μ F, C_{OUT} = 47 μ F, $C_{NR/SS}$ without C_{FF} , and PG pin pulled up to VIN with 100 $k\Omega$, unless otherwise noted. Typical values are at T_J = 25 °C.

Parameter		Condition	Symbol	Min	Тур	Max	Units
Input supply volta	ge range [2]		VIN	1.1		6.5	V
Bias supply voltag	ge range ^[2]	V _{IN} = 1.1 V	V _{BIAS}	3.0		6.5	V
Feedback voltage			V _{FB}		0.8		V
NR/SS pin voltage	Э		V _{NR/SS}		0.8		V
Input supply UVL	O with BIAS	V _{IN} rising with V _{BIAS} = 3.0 V	V _{UVLO1(IN)}		1.02	1.085	V
V _{UVLO1(IN)} hysteresis		V _{BIAS} = 3.0 V	VHYS1(IN)		320		mV
Input supply UVL	O without BIAS	V _{IN} rising	V _{UVLO2(IN)}		1.31	1.39	V
V _{UVLO2(IN)} hysteresis			V _{HYS2(IN)}		250		mV
Bias supply UVLC)	V _{BIAS} rising, V _{IN} = 1.1 V	V _{ULOV(BIAS)}		2.83	2.9	V
V _{UVLO(BIAS)} hysteresis		V _{IN} = 1.1 V	V _{HYS(BIAS)}		290		mV
Output Voltage	Range	Using pin programmability	Vouт	0.8		3.95	V



Parameter		Condition	Symbol	Min	Тур	Max	Units
		Using external resistors	V _{OUT}	0.8		5.15	V
		3.5mm x 3.5 mm pkg 0.8 V \leq V _{OUT} \leq 5.15 V, 5 mA \leq I _{OUT} \leq 2 A, over V _{IN}	Vouт	-1%		1%	
	Accuracy [3][4]	5mm x 5mm pkg $0.8 \text{ V} \leq \text{V}_{\text{OUT}} \leq 5.15 \text{ V},$ $5 \text{ mA} \leq \text{I}_{\text{OUT}} \leq 2 \text{ A, over}$ V_{IN}	Vouт	-1.5%		1.5%	%
	Accuracy with	3.5mm x 3.5mm pkg $1.1V \le V_{IN} \le 2.2 V$, $5 \text{ mA} \le I_{OUT} \le 2 A$, $3 \text{ V} \le V_{BIAS} \le 6.5 \text{ V}$	Vоит	-1%		1%	
	BIAS	5mm x 5mm pkg $1.1V \le V_{IN} \le 2.2 V$, $5 \text{ mA} \le I_{OUT} \le 2 A$, $3 \text{ V} \le V_{BIAS} \le 6.5 \text{ V}$	V _{ОИТ}	-1.5%		1.5%	
Line regulation		$I_{OUT} = 5 \text{ mA},$ 1.4 V \le V_{IN} \le 6.5 V	ΔV _{OUT} / ΔV _{IN}		0.01		mV/V
		$5 \text{ mA} \le I_{OUT} \le 2 \text{ A},$ $3.0 \text{ V} \le V_{BIAS} \le 6.5 \text{ V},$ $V_{IN} = 1.1 \text{ V}$	ΔV _{IN}		0.07		mV/A
Load regulation		5 mA ≤ I _{OUT} ≤ 2 A	ΔΙουτ		0.08		
		$5 \text{ mA} \le I_{\text{OUT}} \le 2 \text{ A},$ $V_{\text{OUT}} = 5.0 \text{ V}$			0.4		
		$V_{IN} = 1.4 \text{ V}, I_{OUT} = 2 \text{ A},$ $V_{FB} = 0.8 \text{ V}$			100	166	
		V _{IN} = 5.4 V, I _{OUT} = 2 A, V _{FB} = 0.8 V			70	166	
Dropout voltage		V _{IN} = 5.6 V, I _{OUT} = 2 A, V _{FB} = 0.8 V	- V _{DO}		80	166	- mV
		V _{IN} = 1.1 V, V _{BIAS} = 5.0 V, I _{OUT} = 2 A, V _{FB} = 0.8 V			70	120	
Output current lim	nit	Vout forced at 0.9 × Vout(nom), VIN = Vout(nom) + 0.4 V	Ішм	2.1	3.4	4.2	А
Short-circuit curre	ent limit	R_{LOAD} = 20 m Ω , under foldback operation	I _{SC}		1		А
		V _{IN} = 6.5 V, I _{OUT} = 5 mA			1.95		mA
GND pin current		V _{IN} = 1.4 V, I _{OUT} = 2 A	I _{GND}		2.4		mA
Sits pin ourion		Shutdown, PG = open, $V_{IN} = 6.5 \text{ V}, V_{EN} = 0.5 \text{ V}$	IGND		1.2	25	μΑ

Notes:

- V_{OUT(nom)} is the calculated V_{OUT} target value from the programmable pins in a fixed configuration. In an adjustable configuration, V_{OUT(nom)} is the expected V_{OUT} value set by the external feedback resistors.
- 2. BIAS supply is required when the V_{IN} supply is below 1.4 V. Conversely, no BIAS supply is required when the V_{IN} supply is higher than or equal to 1.4 V. A BIAS supply helps improve dc and ac performance for $V_{IN} \le 1.4$ V.
- 3. When the device is connected to external feedback resistors at the FB pin, external resistor tolerances are not included.
- 4. The device is not tested under conditions where V_{IN} > V_{OUT} + 1.7 V and I_{OUT} = 2 A, because the power dissipation is higher than the maximum rating of the package.

Table 7 Electrical Specifications (Continued)

Over operating junction temperature range ($T_J = -40$ °C to +125 °C), $V_{IN} = 1.4$ V or $V_{IN} = V_{OUT(nom)} + 0.4$ V (whichever is greater), $V_{BIAS} = open$, $V_{OUT(nom)} = 0.8$ V^[1], $V_{EN} = 1.1$ V, $C_{IN} = 10$ μ F, $C_{OUT} = 47$ μ F, $C_{NR/SS}$ without C_{FF} , and PG pin pulled up to V_{IN} with 100 $k\Omega$, unless otherwise noted. Typical values are at $T_J = 25$ °C.



Parameter	Conditions	Symbol	Min	Тур	Max	Unit
EN pin current	$V_{IN} = 6.5 \text{ V}, V_{EN} = 0 \text{ V}$ and 6.5 V	I _{EN}			0.1	μΑ
BIAS pin current	$\begin{aligned} V_{\text{IN}} &= 1.1 \text{ V}, \text{ V}_{\text{BIAS}} = 6.5 \text{ V}, \\ V_{\text{OUT(nom)}} &= 0.8 \text{ V}, \text{ IouT} = 2 \\ A \end{aligned}$	I _{BIAS}		2.3	3.5	mA
EN pin low-level input voltage (disable device)		VIL(EN)	0		0.5	V
EN pin high-level input voltage (enable device)		VIH(EN)	1.1		6.5	V
PG pin threshold	For falling Vout	V _{IT(PG)}	82% х V _{ОUТ}	88.3% × V _{OUT}	93% х Vоит	V
PG pin hysteresis	For rising V _{OUT}	V _{HYS(PG)}		1% х Vouт		V
PG pin low-level output voltage	V _{OUT} < V _{IT(PG)} , I _{PG} = -1 mA (current into device)	V _{OL(PG)}			0.4	V
PG pin leakage current	Vout > VIT(PG), VPG = 6.5 V	I _{IKG(PG)}			0.1	μΑ
NR/SS pin charging current	$V_{NR/SS} = GND,$ $V_{IN} = 6.5 V$	I _{NR/SS}	4.0	6.2	9.0	μΑ
FB pin leakage current	V _{IN} = 6.5 V	I _{FB}	-100		100	nA
	$V_{IN} - V_{OUT} = 0.4 \text{ V},$ $I_{OUT} = 2 \text{ A},$ $C_{NR/SS} = 100 \text{ nF},$ $C_{FF} = 10 \text{ nF},$ $C_{OUT} = 47\mu\text{F} 10\mu\text{F} 10\mu\text{F} $ $F = 10 \text{ kHz}, V_{OUT} = 0.8 \text{ V},$ $V_{BIAS} = 5.0 \text{ V}$ $V_{IN} - V_{OUT} = 0.4 \text{ V},$ $I_{NR} = 2.2 \text{ A}$			55		dB
	$I_{OUT} = 2 \text{ A},$ $C_{NR/SS} = 100 \text{ nF},$ $C_{FF} = 10 \text{ nF},$ $C_{OUT} = 47 \mu \text{F} 10 \mu \text{F} 10 \mu \text{F}$ F = 500 kHz, $V_{OUT} = 0.8 \text{ V},$ $V_{BIAS} = 5.0 \text{ V}$	PSRR		36		dB
Power-supply ripple rejection	$\begin{split} &V_{IN} - V_{OUT} = 0.4 \text{ V}, \\ &I_{OUT} = 2 \text{ A}, \\ &C_{NR/SS} = 100 \text{ nF}, \\ &C_{FF} = 10 \text{ nF}, \\ &C_{OUT} = 47 \mu F 10 \mu F 10 \mu F \\ &F = 1 \text{MHz}, V_{OUT} = 0.8 \text{ V}, \\ &V_{BIAS} = 5.0 \text{ V} \end{split}$			38		dB
	$\begin{split} &V_{IN} - V_{OUT} = 0.4 \text{ V}, \\ &I_{OUT} = 2 \text{ A}, \\ &C_{NR/SS} = 100 \text{ nF}, \\ &C_{F} = 10 \text{ nF}, \\ &C_{OUT} = 47 \mu F 10 \mu F 10 \mu F \\ &F = 10 \text{ kHz}, V_{OUT} = 5.0 \text{ V} \end{split}$			48		dB
	$V_{IN} - V_{OUT} = 0.4 \text{ V},$ $I_{OUT} = 2 \text{ A},$ $C_{NR/SS} = 100 \text{ nF},$ $C_{FF} = 10 \text{ nF},$ $C_{OUT} = 47\mu\text{F} 10\mu\text{F} 10\mu\text{F}$ $F = 500 \text{ kHz},$ $V_{OUT} = 5.0 \text{ V}$			36		dB



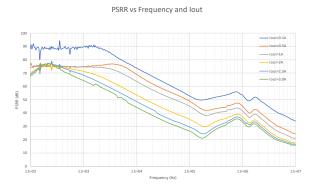
Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
	$V_{IN} - V_{OUT} = 0.4 \text{ V},$ $I_{OUT} = 2 \text{ A},$ $C_{NR/SS} = 100 \text{ nF},$ $C_{FF} = 10 \text{ nF},$ $C_{OUT} = 47\mu\text{F} 10\mu\text{F} 10\mu\text{F}$ $F = 1\text{MHz}, V_{OUT} = 5.0 \text{ V}$			38		dB	
Output noise voltage	$BW = 10 Hz \ to \ 100 \ kHz, \\ V_{IN} = 1.1 \ V, \ V_{OUT} = 0.8 \ V, \\ V_{BIAS} = 5.0 \ V, \ I_{OUT} = 2 \ A, \\ C_{NR/SS} = 100 \ nF, \\ C_{FF} = 10 \ nF, \\ C_{OUT} = 47 \mu F 10 \ \mu F 10 \ \mu F$	Vn		4.3	μV _{RMS}		
· •	BW = 10 Hz to 100 kHz, $V_{OUT} = 5.0 \text{ V, } I_{OUT} = 2 \text{ A,}$ $C_{NR/SS} = 100 \text{ nF,}$ $C_{FF} = 10 \text{ nF,}$ $C_{OUT} = 47\mu\text{F} 10\mu\text{F} 10\mu\text{F}$			7.6		·	
The same of observations as a second or store.	Shutdown, temperature increasing	T		150		°C	
Thermal shutdown temperature	Reset, temperature decreasing	- T _{SD}		130		C	
Operating junction temperature		TJ	-40		125	°C	

Notes:

 V_{OUT(nom)} is the calculated V_{OUT} target value from the programmable pins in a fixed configuration. In an adjustable configuration, V_{OUT(nom)} is the expected V_{OUT} value set by the external feedback resistors.

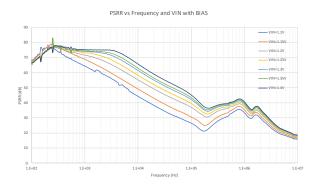
2.1 Typical Characteristics

The following graphs are at TA = 25°C, V_{IN} = 1.4 V or V_{IN} = $V_{OUT(NOM)}$ + 0.4 V (whichever is greater), V_{BIAS} = open, $V_{OUT(NOM)}$ = 0.8 V, V_{EN} = 1.1 V, C_{OUT} = 47 μ F, $C_{NR/SS}$ = 0 nF, C_{FF} = 0 nF, and PG pin pulled up to V_{IN} with 100 $k\Omega$ (unless otherwise noted).



VIN=1.1V, Vout=0.8V, V_{BIAS}=5V, C_{OUT}=(47+10+10)uF, C_{SS}=10nF, C_{FF}=10nF

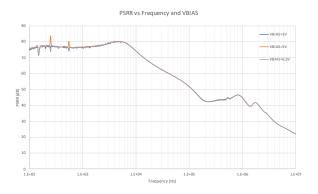
Figure 3 PSRR vs Frequency and IOUT



 $\label{eq:control_state} Vout=0.8V,\ V_{\text{BIAS}}=5V,\ Iout=2A,\ C_{\text{OUT}}=(47+10+10)u\text{F},\ \ C_{\text{SS}}=10n\text{F},\ C_{\text{FF}}=10n\text{F}$

Figure 4 PSRR vs Frequency and V_{IN} with Bias

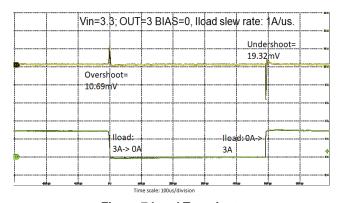




VOUT
PG
EN
Time scale: 1ms/division

Figure 5 PSRR vs Frequency and VBIAS

Figure 6 Power On from EN



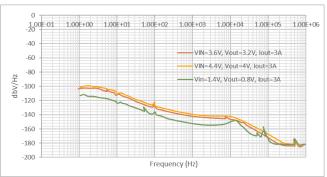


Figure 7 Load Transients

Figure 8 Noise PSD vs Frequency (CNRSS=10nF)

3 Detailed Description

3.1 Overview

The Au8013A is a high-current (2 A), low-noise (4.3 μ VRMS), high accuracy (1%) low-dropout linear voltage regulator (LDO). These features make the device a robust solution to solve many challenging problems in generating a clean, accurate power supply.

The Au8013A has several features that make the device useful in a variety of applications. As detailed in the Functional Block Diagram section, these features include:

- Low-noise, high-PSRR output
- Programmable resistor network
- Optional bias rail
- Power-good output
- Programmable soft-start
- Foldback current limit
- Enable circuitry
- Active discharge
- Thermal protection

Overall, these features make the Au8013A the component of choice because of its versatility and ability to generate a supply for most applications.



3.2 Functional Block Diagram

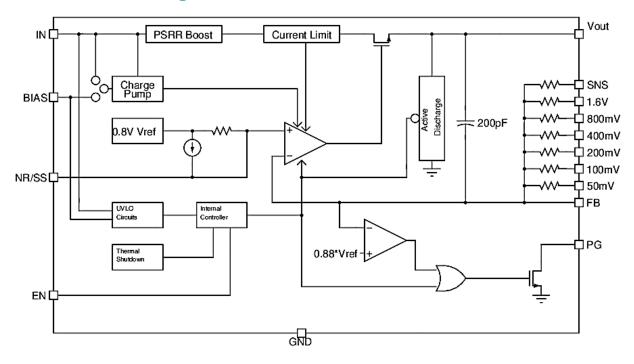


Figure 9 Functional Block Diagram

3.3 Feature Description

3.3.1 Bias Rail

The device features a bias rail to enable low-input voltage, low-output voltage operation by providing power to the internal circuitry of the device. The bias rail is required for operation with $V_{IN} < 1.4$ V. An internal power MUX supplies the greater of either the input voltage or the bias voltage to an internal charge pump to power the internal circuitry.

3.3.2 Power-Good Function

The power-good circuit monitors the voltage at the feedback pin to indicate the status of the output voltage. By connecting a pullup resistor to an external supply, any downstream device can receive power-good as a logic signal that can be used for sequencing. Make sure that the external pullup supply voltage results in a valid logic signal for the receiving device or devices. Using a pullup resistor from 10 k Ω to 100 k Ω is recommended. The use of a feed-forward capacitor (CFF) can cause glitches on start-up, and the power-good circuit may not function normally below the minimum input supply range.

3.3.3 Programmable Soft-Start

Soft-start refers to the ramp-up time of the output voltage during LDO turn-on after EN and UVLO exceed the respective threshold voltage. The noise-reduction capacitor (C_{NR/SS}) serves a dual purpose of both governing output noise reduction and programming the soft-start ramp time during turn-on. The start-up ramp is monotonic and linear in most conditions, however there is a small set of conditions that cause a small initial jump in output voltage.

3.3.4 Internal Current Limit (ILIM)

The internal current limit circuit is used to protect the LDO against high-load current faults or shorting events. During a current-limit event, the LDO sources constant current; therefore, the output voltage falls with decreased load impedance. Thermal shutdown can activate during a current limit event because of the high-



power dissipation typically found in these conditions. To ensure proper operation of the current limit, minimize the inductances to the input and load. Continuous operation in current limit is not recommended.

3.3.5 **Enable**

The enable pin for the Au8013A is active high. The output of the Au8013A is turned on when the enable pin voltage is greater than its rising voltage threshold (1.1 V, max), and is turned off when the enable pin voltage is less than its falling voltage threshold (0.5 V, min). A voltage less than 0.5 V on the enable pin disables all internal circuits. At the next turn-on this voltage ensures a normal start up waveform with in-rush control, provided there is enough time to discharge the output capacitance.

When the enable functionality is not desired, EN must be tied to V_{IN} . However, when the enable functionality is desired, the enable voltage must come after V_{IN} is above $V_{UVLO1(IN)}$ when a BIAS rail is used.

3.3.6 Active Discharge Circuit

The Au8013A has an internal pulldown MOSFET that connects a resistance of several hundred ohms to ground when the device is disabled to actively discharge the output voltage when the device is disabled.

Do not rely on the active discharge circuit for discharging a large amount of output capacitance after the input supply has collapsed because reverse current can possibly flow from the output to the input.

3.3.7 Undervoltage Lockout (UVLO)

The undervoltage lockout (UVLO) circuit monitors the input and bias voltage (V_{IN} and V_{BIAS} , respectively) to prevent the device from turning on before V_{IN} and V_{BIAS} rise above the lockout voltage. The UVLO circuit also disables the output of the device when V_{IN} or V_{BIAS} fall below the lockout voltage. The UVLO circuit responds quickly to glitches on V_{IN} or V_{BIAS} and attempts to disable the output of the device if either of these rails collapse. As a result of the fast response time of the input supply UVLO circuit, fast and short line transients well below the input supply UVLO falling threshold can cause momentary glitches when asserted or when recovered from the transient.

3.3.8 Thermal Protection

The Au8013A contains a thermal shutdown protection circuit to disable the device when thermal junction temperature (T_J) of the main pass-FET exceeds 150°C (typical). Thermal shutdown hysteresis assures that the LDO resets again (turns on) when the temperature falls to 130°C (typical). The thermal time constant of the semiconductor die is fairly short, and thus the device cycles on and off when thermal shutdown is reached until the power dissipation is reduced. For reliable operation, limit the junction temperature to a maximum of 125 °C. Operation above 125 °C can cause the device to exceed its operational specifications. Although the internal protection circuitry of the Au8013A is designed to protect against thermal overload conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the Au8013A into thermal shutdown or above a junction temperature of 125 °C reduces long-term reliability.

3.4 Device Functional Modes

3.4.1 Operation with 1.1 $V \le V_{IN} < 1.4 V$

The Au8013A requires a bias voltage on the BIAS pin greater than or equal to 3.0 V if the high-current input supply voltage is between 1.1 V to 1.4 V. The bias voltage pin consumes 2.4 mA, nominally.

3.4.2 Operation with 1.4 V \leq V_{IN} \leq 6.5 V

If the input voltage is equal to or exceeds 1.4 V, no BIAS voltage is required. The Au8013A is powered from either the input supply or the BIAS supply, whichever is greater.



3.4.3 Shutdown

Shutting down the device reduces the ground current of the device to a maximum of 25 µA.

4 Application and Implementation

NOTE: Information in the following applications sections is not part of the Aura Semiconductor component specification, and Aura Semiconductor does not warrant its accuracy or completeness. Aura Semiconductor's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

4.1 Application Information

The Au8013A is a linear voltage regulator with an input range of 1.1 V to 6.5 V and an output voltage range of 0.8 V to 5.0 V with a 1% accuracy and a 2 A maximum output current. The Au8013A has an integrated charge pump for ease of use and an external bias rail to allow for the lowest dropout across the entire output voltage range.

4.1.1 Recommended Capacitor Types

The Au8013A is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input, output, and noise-reduction pin (NR, pin 13). Regardless of the ceramic capacitor type selected, ceramic capacitance varies with operating voltage and temperature. As a rule of thumb, derate ceramic capacitors by at least 50%. The input and output capacitors recommended herein account for a capacitance derating of approximately 50%, but at high V_{IN} and V_{OUT} conditions (that is, $V_{IN} = 5.5 \text{ V}$ to $V_{OUT} = 5.0 \text{ V}$) the derating can be greater than 50% and must be taken into consideration.

4.1.2 Input and Output Capacitor Requirements (C_{IN} and C_{OUT})

The Au8013A is designed and characterized for operation with ceramic capacitors of 47 μ F or greater (22 μ F or greater of capacitance) at the output and 10 μ F or greater (5 μ F or greater of capacitance) at the input. Place the capacitors as close to the pins as possible to minimize ringing.

4.1.3 Noise-Reduction and Soft-Start Capacitor (C_{NR/SS})

The Au8013A features a programmable, monotonic, voltage-controlled soft-start that is set with an external capacitor (C_{NR/SS}). The use of an external C_{NR/SS} is highly recommended, especially to minimize in-rush current into the output capacitors. This soft-start eliminates power-up initialization problems when powering field-programmable processors. The controlled voltage ramp of the output also reduces peak in-rush current during start-up, minimizing start-up transients to the input power bus.

Soft-start ramp time can be calculated with Equation 1:

$$t_{SS} = (V_{NR/SS} \times C_{NR/SS}) / I_{NR/SS}$$
(1)

Note that INR/SS is provided has a typical value of 6 μ A.

The noise-reduction capacitor, in conjunction with the noise-reduction resistor, forms a low pass filter (LPF) that filters out the noise from the reference before being gained up with the error amplifier, thereby reducing the device noise floor. The LPF is a single-pole filter and the cutoff frequency can be calculated with Equation 2. The typical value of RNR is 1 M Ω . Increasing the CNR/SS capacitor has a greater affect because the output voltage increases when the noise from the reference is gained up even more at higher output voltages. For low-noise applications, a 10 nF to 1 μ F CNR/SS is recommended.



fcutoff = 1 / $(2 \times \pi \times R_{NR} \times C_{NR/SS})$

(2)

4.1.4 Feed-Forward Capacitor (C_{FF})

Although a feed-forward capacitor (C_{FF}) from the FB pin to the OUT pin is not required to achieve stability, a 10 nF external feed-forward capacitor optimizes the transient, noise, and PSRR performance. A higher capacitance C_{FF} can be used; however, the start-up time is longer and the power-good signal can incorrectly indicate that the output voltage is settled.

4.1.5 Optimizing Noise and PSRR

The ultra-low noise floor and PSRR of the device can be improved by careful selection of:

- C_{NR/SS} for the low-frequency range
- · CFF in the mid-band frequency range
- Cout for the high-frequency range
- V_{IN} V_{OUT} for all frequencies, and

A larger noise-reduction capacitor improves low-frequency PSRR by filtering any noise coupling from the input into the reference. The feed-forward capacitor can be optimized to place a pole-zero pair near the edge of the loop bandwidth and push out the loop bandwidth, thus improving mid-band PSRR. Larger output capacitors and various output capacitors can be used to improve high-frequency PSRR.

4.1.6 Adjustable Operation

The Au8013A can be used either with the internal programmable output network or by using external resistors. Using the programmable output network allows the Au8013A to be programmed from 0.8 V to 3.95 V. To extend this output voltage range to 5.0 V, external resistors must be used. This configuration is referred to as the adjustable configuration of the Au8013A throughout this document. Regardless of whether the internal resistor network or the external resistors are used, the output voltage is set by the two resistors, as shown in Figure 10. Using the internal resistor ensures a 1% accuracy and minimizes the number of external components.



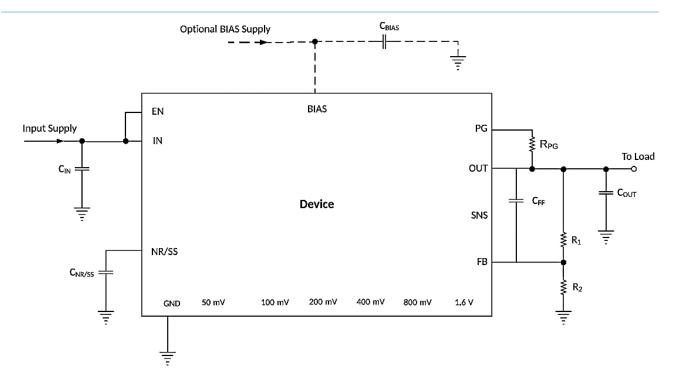


Figure 10 Adjustable Operation

R1 and R2 can be calculated for any output voltage range using Equation 3. This resistive network must provide a current equal to or greater than 5 μ A for dc accuracy. Using an R1 of 12.1 k Ω is recommended to optimize the noise and PSRR.

$$V_{OUT} = V_{NR/SS} \times (1 + R1 / R2)$$
(3)

Table 8 shows the resistor combinations required to achieve several common rails using standard 1% tolerance resistors.

V (A)	Feedback Resistor Values				
Vout(NOM) (V)	R ₁ (kΩ)	R ₂ (kΩ)			
0.9	12.1	97.6			
1.00	12.1	48.7			
1.10	12.1	32.4			
1.20	12.1	24.3			
1.50	12.1	13.7			
1.80	12.1	9.76			
1.90	12.1	8.87			
2.50	12.1	5.76			
2.85	12.1	4.75			
3.00	12.1	4.42			
3.30	12.1	3.83			

Table 8 Recommended Feedback-Resistor Values

4.1.7 Pin Programmable Output Configuration

The output voltage of Au8013A can be set by an internal resistor network. The internal resistor network is accessed through pins 5,6,7,9,10,11. The default output voltage when all pin-programmable pins are floated is 0.8 V. Connecting the pin-programmable pins to GND raises the output voltage from 0.8V by the amount described in the pin's name.



Table 9 P	in Programability	AnchloV tunture av
I able 3 F	III FIUUI AIIIADIIILV V	vs Outbut voltage

Pin	Additive increment in output voltage
Pin5 (50 mV)	50 mV
Pin6 (100 mV)	100 mV
Pin7 (200 mV)	200 mV
Pin9 (400 mV)	400 mV
Pin10 (800 mV)	800 mV
Pin11 (1.6 V)	1.6 V

4.2 Typical Applications

4.2.1 Low-Input, Low-Output Voltage Conditions

This section discusses the implementation of the Au8013A using the programmable output configuration to regulate a 3.0 A load requiring good PSRR at high frequency with low-noise at 0.9 V using a 1.2 V input voltage and a 5.0 V bias supply. The schematic for this typical application circuit is provided in

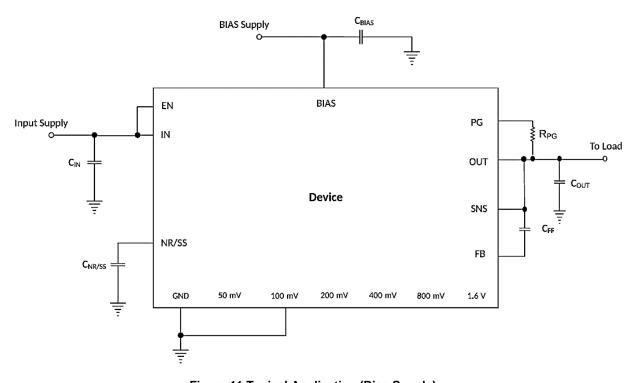


Figure 11 Typical Application (Bias Supply)

4.2.2 Typical Application for a 5.0-V Rail

This section discusses the implementation of the Au8013A using an adjustable feedback network to regulate a 2 A load requiring good PSRR at high frequency with low-noise at an output voltage of 5.0 V.



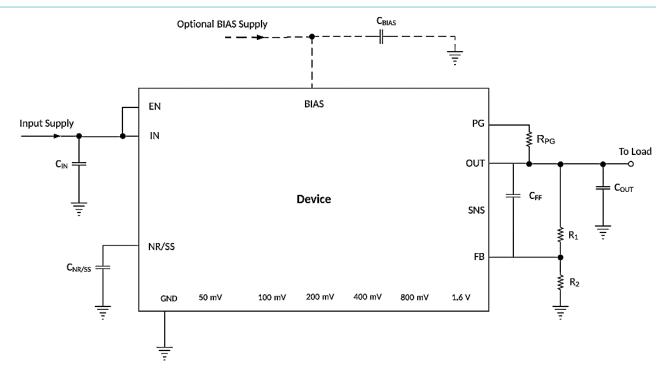
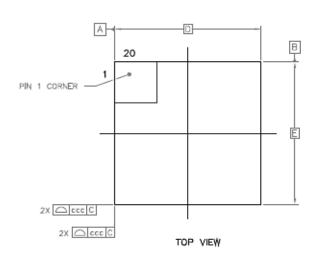


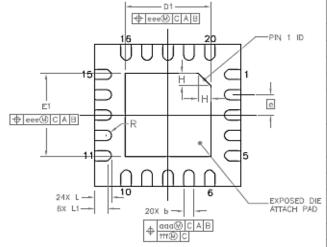
Figure 12 Typical Application



5 Package Information

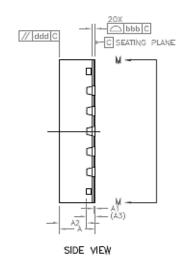
3.5mm x 3.5mm 20 Pin QFN package.





BOTTOM VIEW

VIEW M-M



MILLIMETER DESCRIPTION SYMBOL MIN NOM MAX TOTAL THICKNESS 0.80 0.85 0.90 STAND OFF 0.035 0.05 Α1 0 MOLD THICKNESS A2 0.65 0.67 0.203_{REF} MATERIAL THICKNESS А3 3.5 3.6 D 3.4 PACKAGE SIZE Ε 3.5 3.6 D1 1.95 2.05 2.15 EP SIZE E1 1.95 2.05 2.15 LEAD LENGTH L 0.30 0.40 0.50 LEAD PITCH 0.5_{BSC} LEAD WIDTH 0.20 0.25 0.30 ь LEAD POSITION OFFSET 0.10 aaa LEAD COPLANARITY bbb 0.08 PACKAGE EDGE PROFILE 0.15 ccc MOLD FLATNESS ddd 0.10 EP POSITION OFFSET 0.10 eee fff 0.05 L1 0.313

R

Н

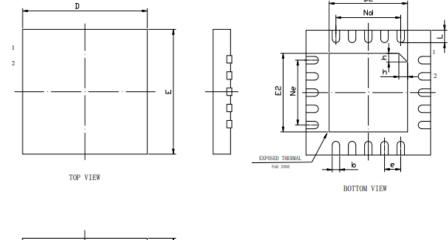
PIN 1 DIMENSION

0.125

0.3 REF



5mm x 5mm 20 Pin QFN Package



SYMBOL	MILLIMETER				
STMBOL	MIN	NOM	MAX		
A	0.85	0.90	0.95		
A1	_	0.02	0.05		
b	0. 25	0.30	0.35		
c	0.18	0.20	0.25		
D	4. 90	5. 00	5. 10		
D2	3. 05	3. 15	3. 25		
e	0. 65BSC				
Ne	2	2. 60BSC			
Nd	2	2. 60BSC			
E	4. 90	5. 00	5. 10		
E2	3, 05	3, 15	3, 25		
L	0.45	0.55 0.35	0.65		
h	0.30		0.40		
L/F载体尺寸					

4

Figure 13 Package Information

Package MSL rating: MSL2 for both packages.

Tape and Reel Info:

Device	Package type	Pins	SPQ 最小 包装 数量	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
Au8013EA5-QNR	QFN 5x5	20	4000	330	12.3	5.25	5.25	1.1	8	12	Q2 (Top Right)
Au8013EA3-QNR	QFN 3.5x3.5	20	4000	330	12.3	3.8	3.8	1.15	8	12	Q2 (Top Right)



6 Ordering Information

Table 10 Ordering Information

Ordering Part Number (OPN)	Marking	Package	Shipping Package	Temperature Range	
Au8013EA3-QNR	Au8013EA3	20-Pin QFN	Tape and Reel	-40°C to 125°C	
AU0013EA3-QIVIX	AddotaLAS	3.5mmx 3.5mm	rape and Neer		
Au8013EA5-QNR	Au8013EA5	20-Pin QFN	Tape and Reel	-40°C to 125°C	
AU0013EA3-QINK	AUGUTSEAS	5mmx 5mm	Tape and Neel	-40 C to 125 C	
Au8013EA5- EVM			Evaluation board		
Au8013EA3- EVM			Evaluation board		

7 Revision History

Table 11 Revision History

Version Number		Description	Author	
1.0	4 th Dec 2021	Release version 1.0	AuraSemi	

8 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

9 Contact Information

For more information visit www.aurasemi.com

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